

V_{DSS}	200V
$R_{DS(on)}$ (Max.)	870m Ω
I_D	3.0A
P_D	20W

●Features

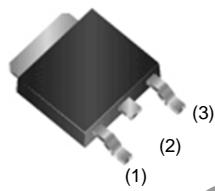
- 1) Low on-resistance.
- 2) Fast switching speed.
- 3) Drive circuits can be simple.
- 4) Parallel use is easy.
- 5) Pb-free lead plating ; RoHS compliant
- 6) 100% Avalanche tested

●Application

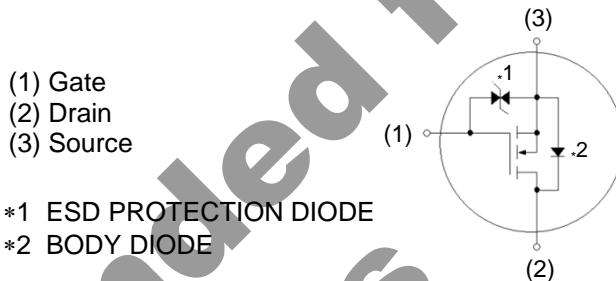
Switching Power Supply
 Automotive Motor Drive
 Automotive Solenoid Drive

●Outline

CPT3
 (SC-63)
 <SOT-428>



●Inner circuit



●Packaging specifications

Type	Packaging	Taping
	Reel size (mm)	330
	Tape width (mm)	16
	Basic ordering unit (pcs)	2,500
	Taping code	TL
	Marking	N03N20

●Absolute maximum ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Drain - Source voltage	V_{DSS}	200	V
Continuous drain current	I_D * ¹	± 3.0	A
	I_D * ¹	± 1.6	A
Pulsed drain current	$I_{D,pulse}$ * ²	± 6.0	A
Gate - Source voltage	V_{GSS}	± 30	V
Avalanche energy, single pulse	E_{AS} * ³	0.73	mJ
Avalanche current	I_{AR} * ³	1.5	A
Power dissipation	P_D	20	W
	P_D	0.85	W
Junction temperature	T_j	150	°C
Range of storage temperature	T_{stg}	-55 to +150	°C

● Thermal resistance

Parameter	Symbol	Values			Unit
		Min.	Typ.	Max.	
Thermal resistance, junction - case	R _{thJC}	-	-	6.25	°C/W
Thermal resistance, junction - ambient ^{*4}	R _{thJA}	-	-	147	°C/W
Soldering temperature, wavesoldering for 10s	T _{sold}	-	-	265	°C

● Electrical characteristics (T_a = 25°C)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Drain - Source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 1mA	200	-	-	V
Zero gate voltage drain current	I _{DSS}	V _{DS} = 200V, V _{GS} = 0V T _j = 25°C	-	-	10	μA
		V _{DS} = 200V, V _{GS} = 0V T _j = 125°C	-	-	100	
Gate - Source leakage current	I _{GSS}	V _{GS} = ±30V, V _{DS} = 0V	-	-	±10	nA
Gate threshold voltage	V _{GS(th)}	V _{DS} = 10V, I _D = 1mA	3.2	-	5.2	V
Static drain - source on - state resistance	R _{DS(on)} ^{*5}	V _{GS} = 10V, I _D = 1.5A	-	620	870	mΩ
		V _{GS} = 10V, I _D = 1.5A T _j = 125°C	-	1150	1610	
Forward transfer admittance	g _{fs}	V _{DS} = 10V, I _D = 1.5A	0.75	1.50	-	S

● Electrical characteristics($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Input capacitance	C_{iss}	$V_{GS} = 0\text{V}$ $V_{DS} = 25\text{V}$ $f = 1\text{MHz}$	-	270	-	pF
Output capacitance	C_{oss}		-	30	-	
Reverse transfer capacitance	C_{rss}		-	10	-	
Turn - on delay time	$t_{d(on)}^{*5}$	$V_{DD} \approx 100\text{V}, V_{GS} = 10\text{V}$ $I_D = 1.5\text{A}$ $R_L = 12\Omega$ $R_G = 10\Omega$	-	13	-	ns
Rise time	t_r^{*5}		-	13	-	
Turn - off delay time	$t_{d(off)}^{*5}$		-	18	-	
Fall time	t_f^{*5}		-	17	-	

● Gate Charge characteristics($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Total gate charge	Q_g^{*5}	$V_{DD} \approx 100\text{V}$ $I_D = 3.0\text{A}$ $V_{GS} = 10\text{V}$	-	6.7	-	nC
Gate - Source charge	Q_{gs}^{*5}		-	2.7	-	
Gate - Drain charge	Q_{gd}^{*5}		-	2.4	-	
Gate plateau voltage	$V_{(plateau)}$	$V_{DD} \approx 100\text{V}, I_D = 3\text{A}$	-	7.2	-	V

● Body diode electrical characteristics (Source-Drain)($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Continuous source current	I_s^{*1}	$T_c = 25^\circ\text{C}$	-	-	3.0	A
Pulsed source current	I_{SM}^{*2}		-	-	6.0	A
Forward voltage	V_{SD}^{*5}	$V_{GS} = 0\text{V}, I_S = 3.0\text{A}$	-	-	1.5	V
Reverse recovery time	t_{rr}^{*5}	$I_S = 1.5\text{A}$ $di/dt = 100\text{A}/\mu\text{s}$	-	55	-	ns
Reverse recovery charge	Q_{rr}^{*5}		-	11	-	nC

*1 Limited only by maximum temperature allowed.

*2 $P_w \leq 10\mu\text{s}$, Duty cycle $\leq 1\%$

*3 $L \approx 500\mu\text{H}$, $V_{DD} = 50\text{V}$, $R_g = 25\Omega$, starting $T_j = 25^\circ\text{C}$

*4 Mounted on a epoxy PCB FR4 (20mm × 30mm × 0.8mm)

*5 Pulsed

● Electrical characteristic curves

Fig.1 Power Dissipation Derating Curve

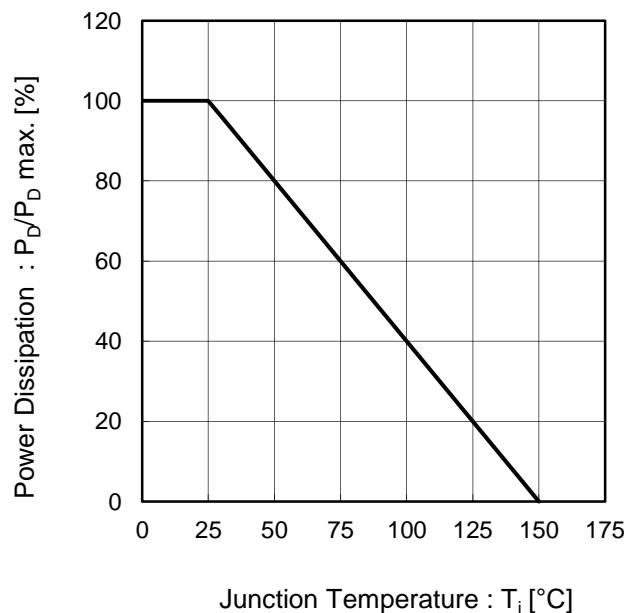


Fig.2 Maximum Safe Operating Area

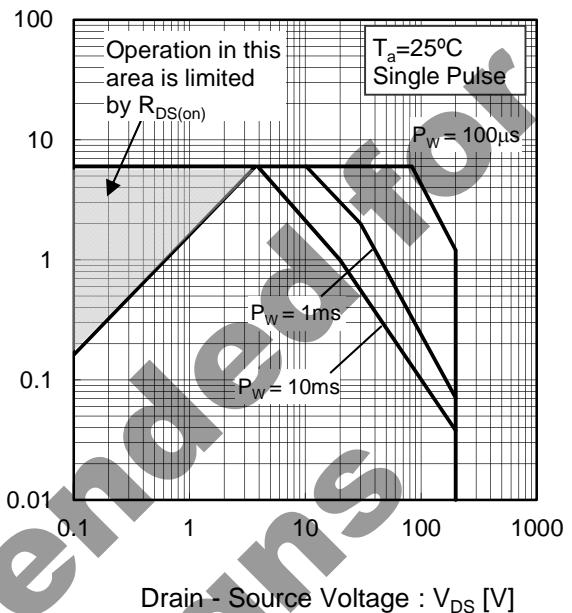
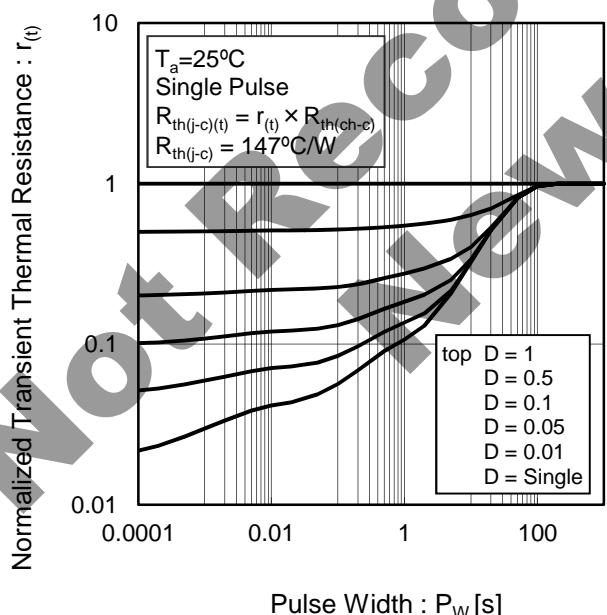


Fig.3 Normalized Transient Thermal Resistance vs. Pulse Width



● Electrical characteristic curves

Fig.4 Avalanche Current vs Inductive Load

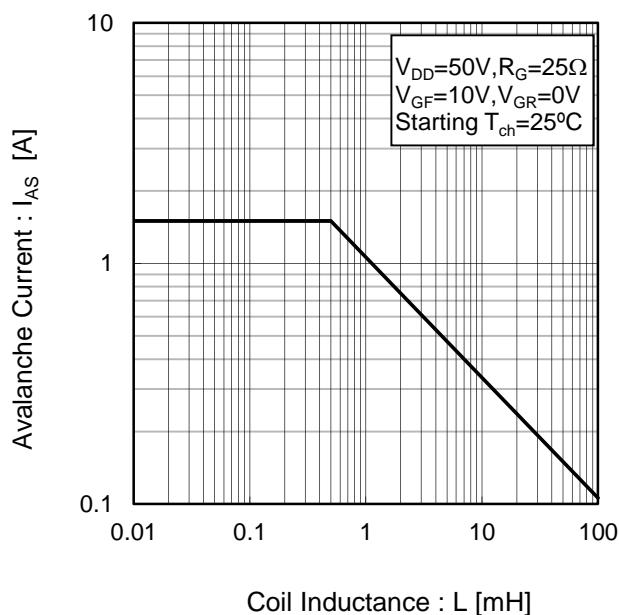


Fig.5 Avalanche Energy Derating Curve vs Junction Temperature

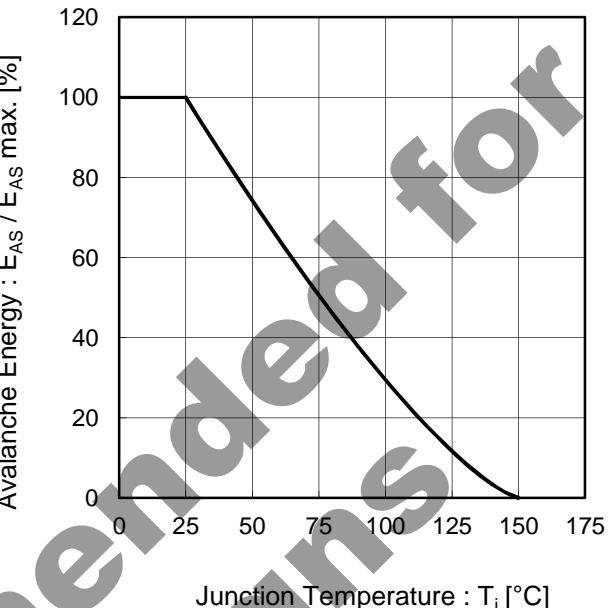


Fig.6 Typical Output Characteristics(I)

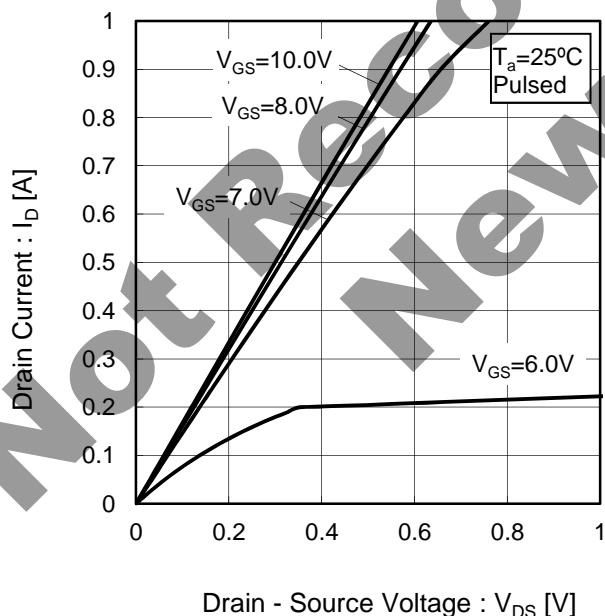
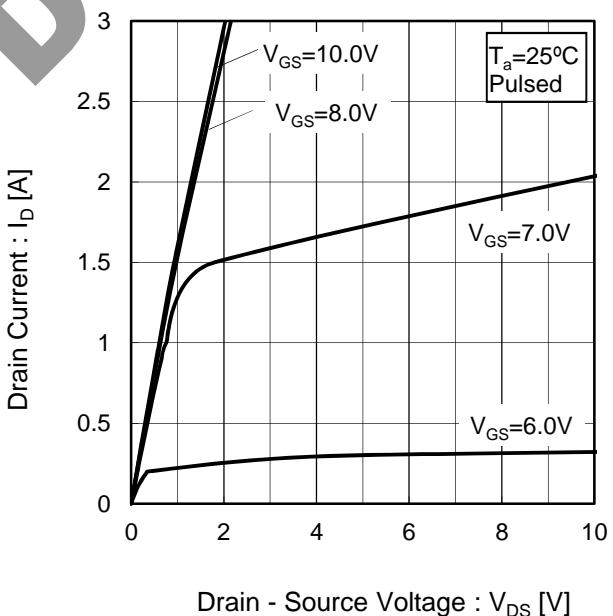


Fig.7 Typical Output Characteristics(II)



● Electrical characteristic curves

Fig.8 Breakdown Voltage
vs. Junction Temperature

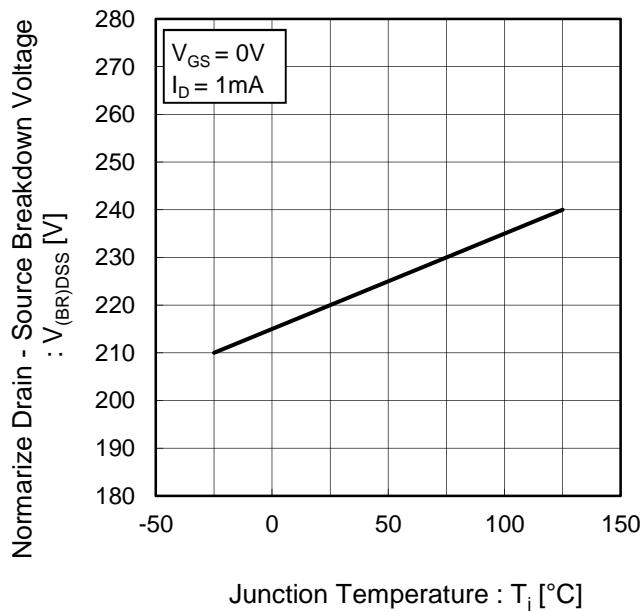


Fig.9 Typical Transfer Characteristics

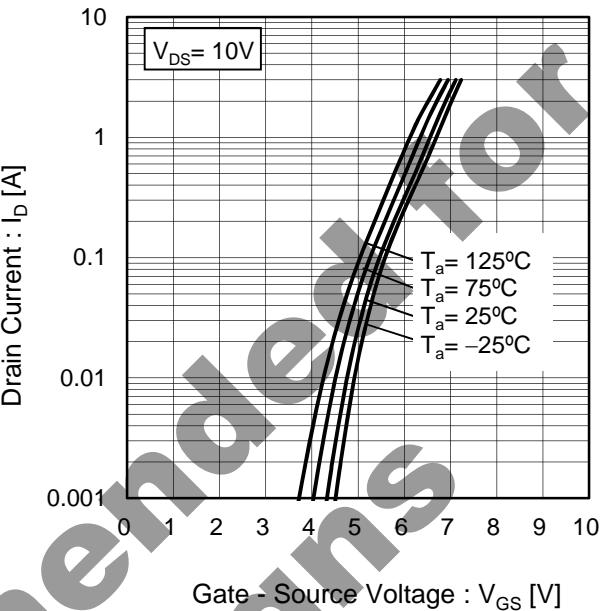


Fig.10 Gate Threshold Voltage
vs. Junction Temperature

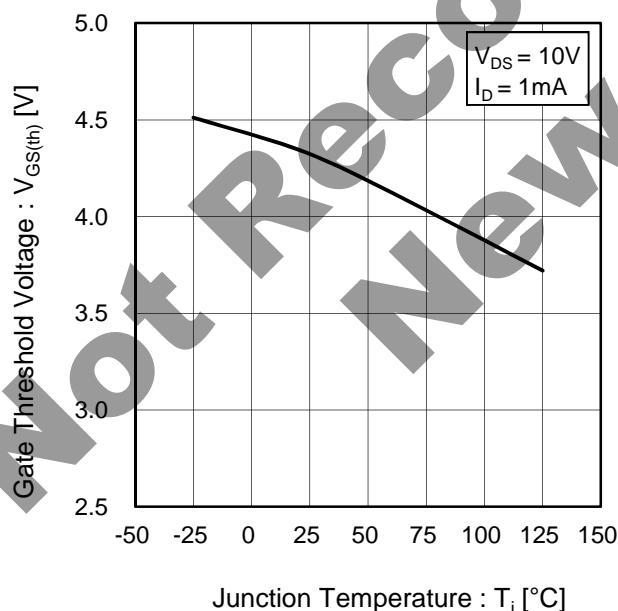
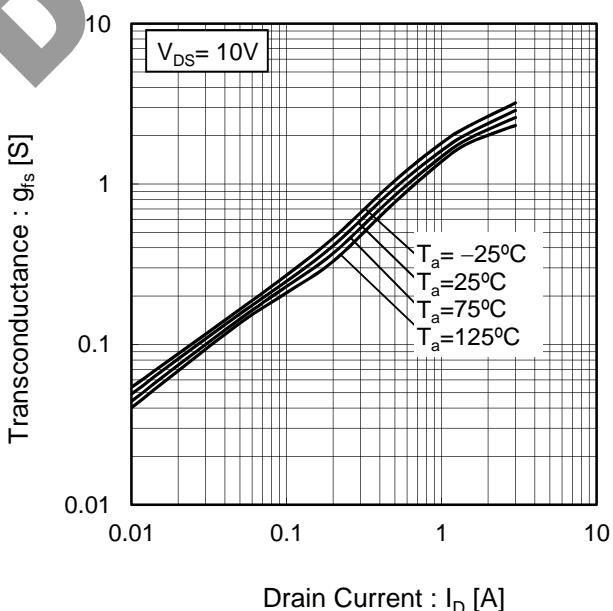


Fig.11 Transconductance vs. Drain Current



● Electrical characteristic curves

Fig.12 Static Drain - Source On - State Resistance vs. Gate Source Voltage

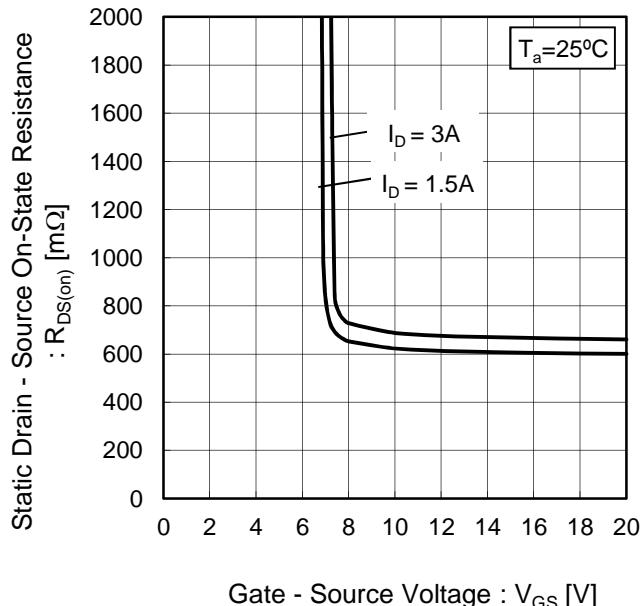


Fig.13 Static Drain - Source On - State Resistance vs. Drain Current(I_D)

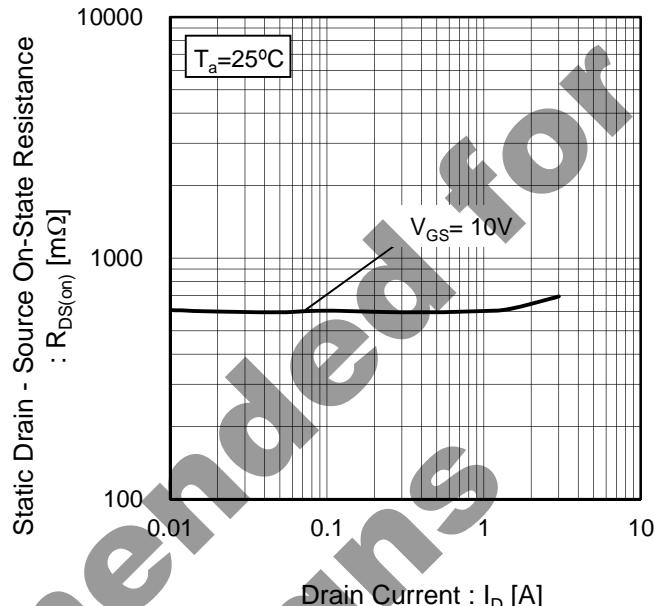
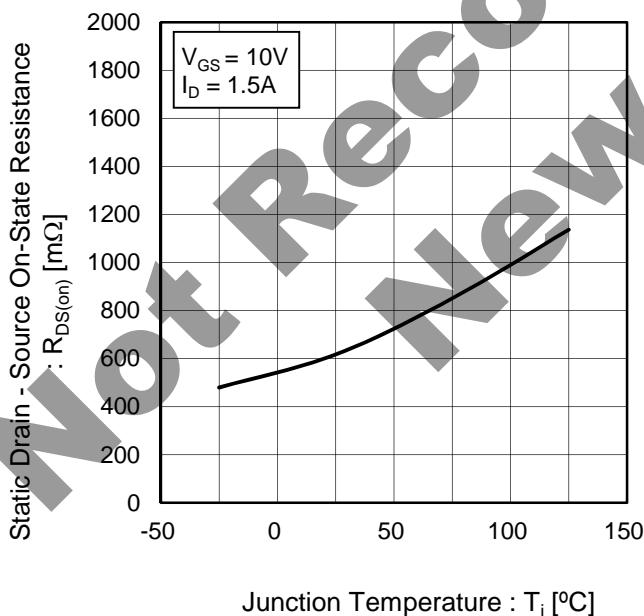


Fig.14 Static Drain - Source On - State Resistance vs. Junction Temperature



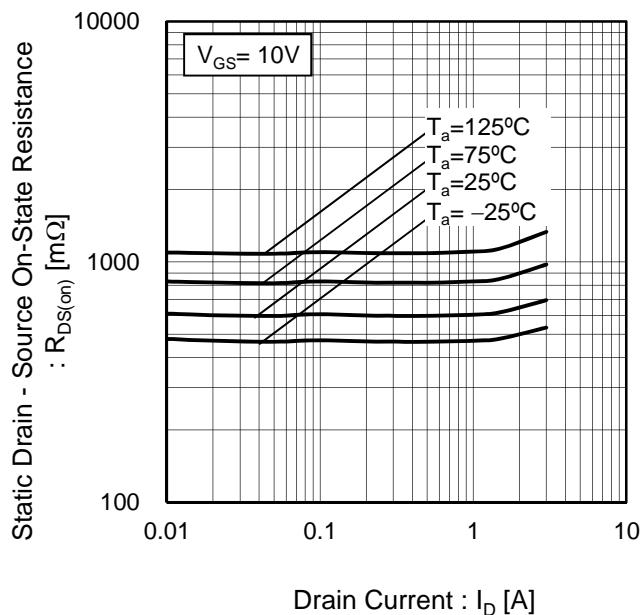
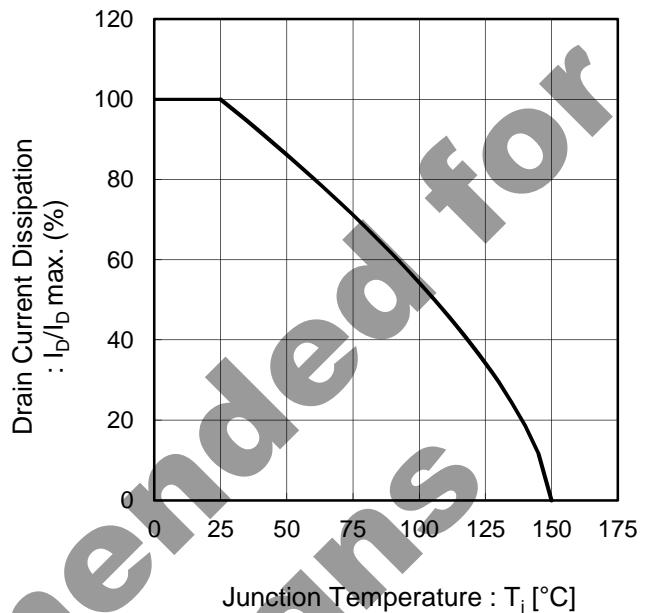
●Electrical characteristic curvesFig.15 Static Drain - Source On - State Resistance vs. Drain Current(I_D)

Fig.16 Drain Current Derating Curve



● Electrical characteristic curves

Fig.17 Typical Capacitance vs. Drain - Source Voltage

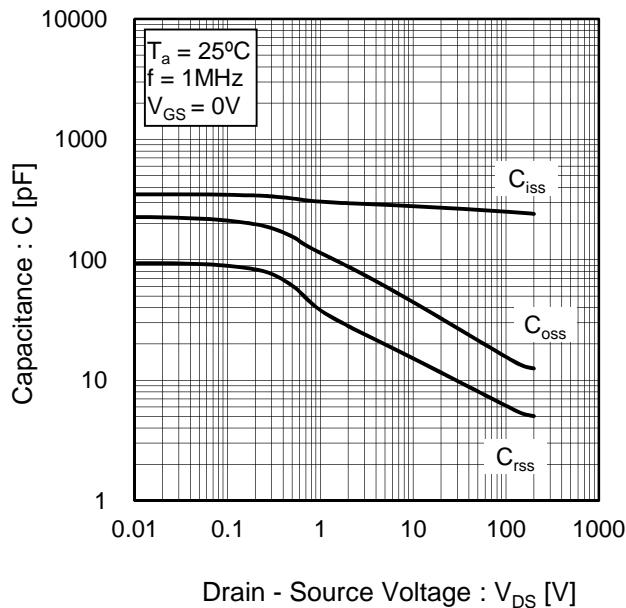


Fig.18 Switching Characteristics

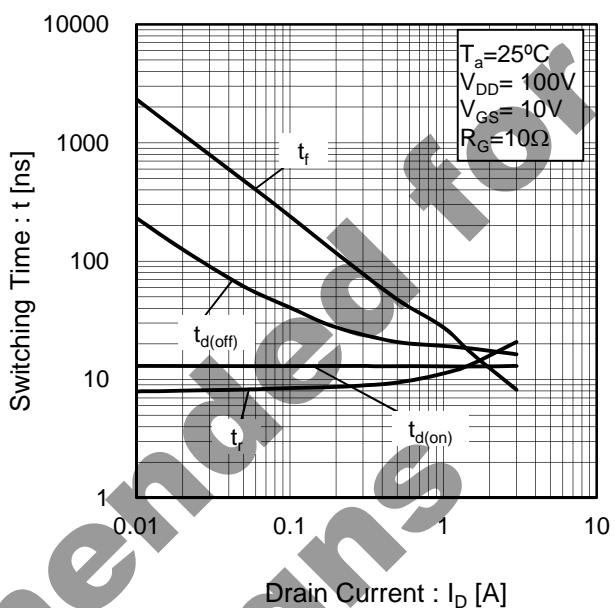
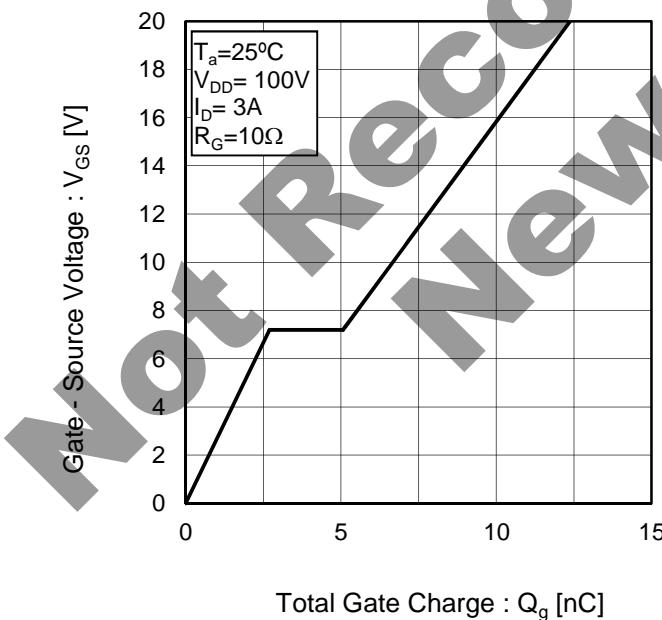


Fig.19 Dynamic Input Characteristics



●Electrical characteristic curves

Fig.20 Source Current
vs. Source - Drain Voltage

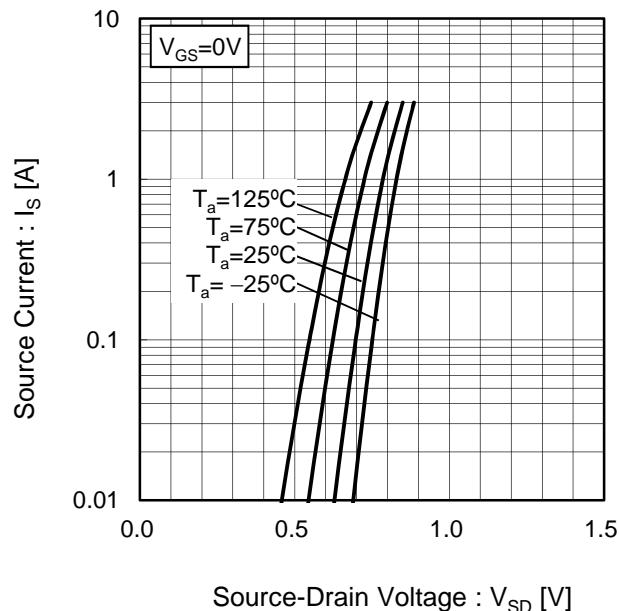
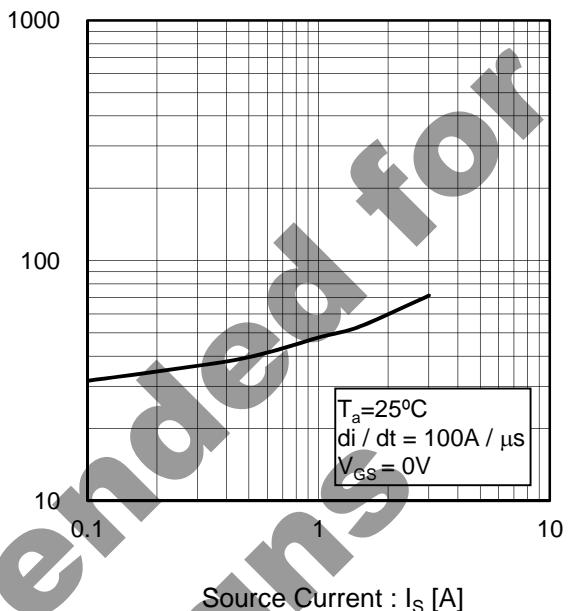


Fig21 Reverse Recovery Time
vs. Source Current



Not Recommended for
New Designs

●Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

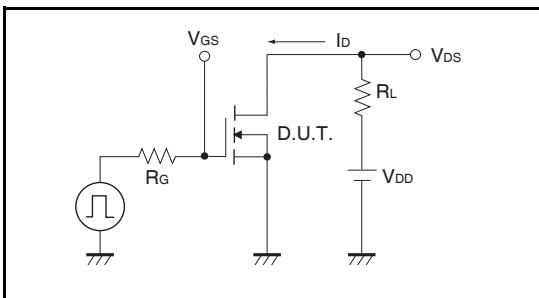


Fig.1-2 Switching Waveforms

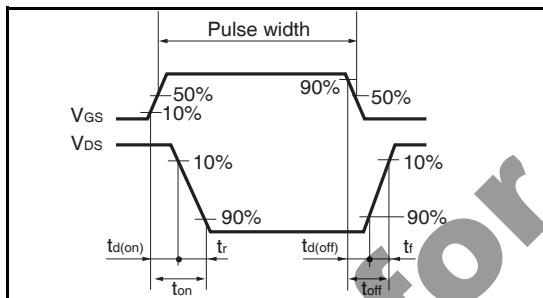


Fig.2-1 Gate Charge Measurement Circuit

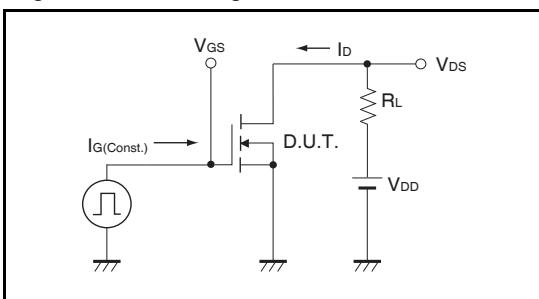


Fig.2-2 Gate Charge Waveform

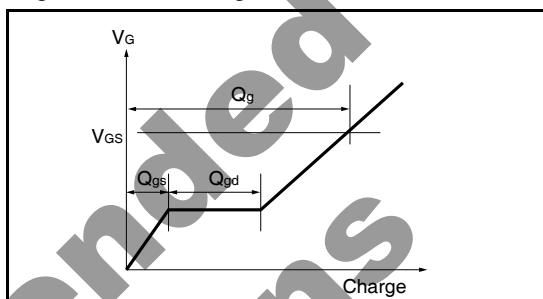


Fig.3-1 Avalanche Measurement Circuit

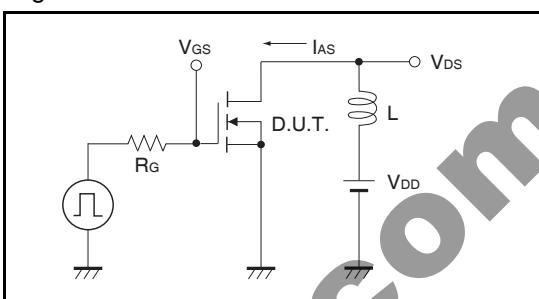
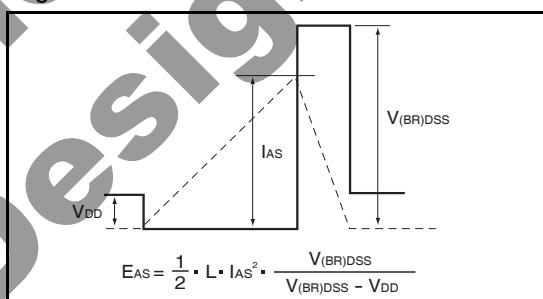


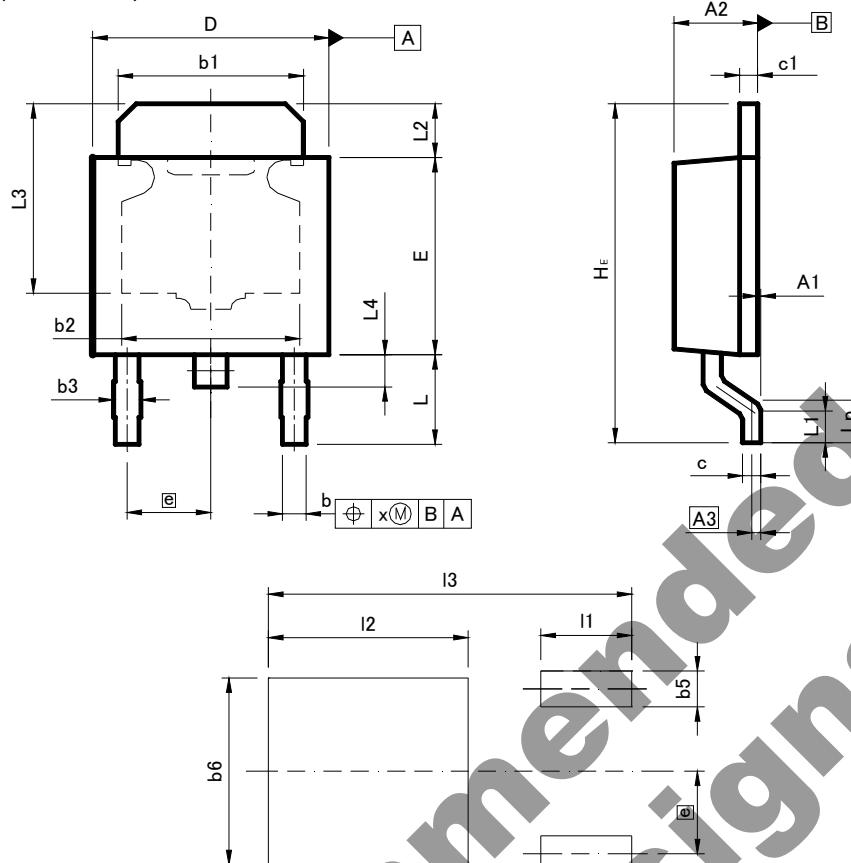
Fig.3-2 Avalanche Waveform



Not Recommended for New Designs

●Dimensions (Unit : mm)

CPT3



DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A1	0.00	0.15	0	0.006
A2	2.20	2.50	0.087	0.098
A3	0.25		0.01	
b	0.55	0.75	0.022	0.03
b1	5.00	5.30	0.197	0.209
b2	5.00		0.20	
b3	0.75		0.03	
c	0.40	0.60	0.016	0.024
c1	0.40	0.60	0.016	0.024
D	6.30	6.70	0.248	0.264
E	5.40	5.80	0.213	0.228
e	2.30		0.09	
H_E	9.00	10.00	0.354	0.394
L	2.20	2.80	0.087	0.11
L1	0.80	1.40	0.031	0.055
L2	1.20	1.80	0.047	0.071
L3	5.30		0.209	
L4	0.90		0.035	
Lp	1.00	1.60	0.039	0.063
x	-	0.25	-	0.01

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
b5	-	1.00	-	0.04
b6	-	5.20	-	0.205
I1	-	2.50	-	0.098
I2	-	5.50	-	0.217
I3	-	10.00	-	0.394

Dimension in mm/inches

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